

# BC549C, BC550C

## Low Noise Transistors

### NPN Silicon

#### Features

- These are Pb-Free Devices\*

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC549C BC550C	$V_{CEO}$	30 45	Vdc
Collector-Base Voltage BC549C BC550C	$V_{CBO}$	30 50	Vdc
Emitter-Base Voltage	$V_{EBO}$	5.0	Vdc
Collector Current - Continuous	$I_C$	100	Vdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above = $25^\circ\text{C}$	$P_D$	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above = $25^\circ\text{C}$	$P_D$	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

#### THERMAL CHARACTERISTICS

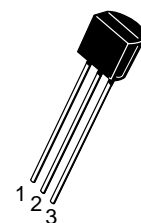
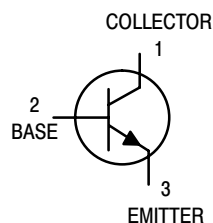
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

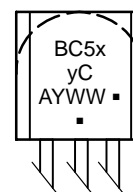
<http://onsemi.com>



TO-92  
CASE 29  
STYLE 17

STRAIGHT LEAD  
BULK PACK

#### MARKING DIAGRAM



BC5xyC = Device Code

x = 4 or 5

y = 9 or 0

A = Assembly Location

Y = Year

WW = Work Week

▪ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping
BC549CG	TO-92 (Pb-Free)	5000 Units / Bulk
BC550CG	TO-92 (Pb-Free)	5000 Units / Bulk

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# BC549C, BC550C

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Breakdown Voltage ( $I_C = 10\text{ mAdc}$ , $I_B = 0$ )	$V_{(BR)CEO}$	45	–	–	Vdc
Collector–Base Breakdown Voltage ( $I_C = 10\text{ }\mu\text{Adc}$ , $I_E = 0$ )	$V_{(BR)CBO}$	50	–	–	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 10\text{ }\mu\text{Adc}$ , $I_C = 0$ )	$V_{(BR)EBO}$	5.0	–	–	Vdc
Collector Cutoff Current ( $V_{CB} = 30\text{ V}$ , $I_E = 0$ ) ( $V_{CB} = 30\text{ V}$ , $I_E = 0$ , $T_A = +125^\circ\text{C}$ )	$I_{CBO}$	– –	– –	15 5.0	nAdc $\mu\text{Adc}$
Emitter Cutoff Current ( $V_{EB} = 4.0\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	–	–	15	nAdc

## ON CHARACTERISTICS

DC Current Gain ( $I_C = 10\text{ }\mu\text{Adc}$ , $V_{CE} = 5.0\text{ Vdc}$ ) ( $I_C = 2.0\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ )	$h_{FE}$	100 420	270 500	– 800	–
Collector–Emitter Saturation Voltage ( $I_C = 10\text{ mAdc}$ , $I_B = 0.5\text{ mAdc}$ ) ( $I_C = 10\text{ mAdc}$ , $I_B = \text{see note 1}$ ) ( $I_C = 100\text{ mAdc}$ , $I_B = 5.0\text{ mAdc}$ , see note 2)	$V_{CE(sat)}$	– – –	0.075 0.3 0.25	0.25 0.6 0.6	Vdc
Base–Emitter Saturation Voltage ( $I_C = 100\text{ mAdc}$ , $I_B = 5.0\text{ mAdc}$ )	$V_{BE(sat)}$	–	1.1	–	Vdc
Base–Emitter On Voltage ( $I_C = 10\text{ }\mu\text{Adc}$ , $V_{CE} = 5.0\text{ Vdc}$ ) ( $I_C = 100\text{ }\mu\text{Adc}$ , $V_{CE} = 5.0\text{ Vdc}$ ) ( $I_C = 2.0\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ )	$V_{BE(on)}$	– – 0.55	0.52 0.55 0.62	– – 0.7	Vdc

## SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	–	250	–	MHz
Collector–Base Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{cbo}$	–	2.5	–	pF
Small–Signal Current Gain ( $I_C = 2.0\text{ mAdc}$ , $V_{CE} = 5.0\text{ V}$ , $f = 1.0\text{ kHz}$ )	$h_{fe}$	450	600	900	–
Noise Figure ( $I_C = 200\text{ }\mu\text{Adc}$ , $V_{CE} = 5.0\text{ Vdc}$ , $R_S = 2.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ ) ( $I_C = 200\text{ }\mu\text{Adc}$ , $V_{CE} = 5.0\text{ Vdc}$ , $R_S = 100\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ )	$NF_1$ $NF_2$	– –	0.6 –	2.5 10	dB

- $I_B$  is value for which  $I_C = 11\text{ mA}$  at  $V_{CE} = 1.0\text{ V}$ .
- Pulse test =  $300\text{ }\mu\text{s}$  – Duty cycle = 2%.

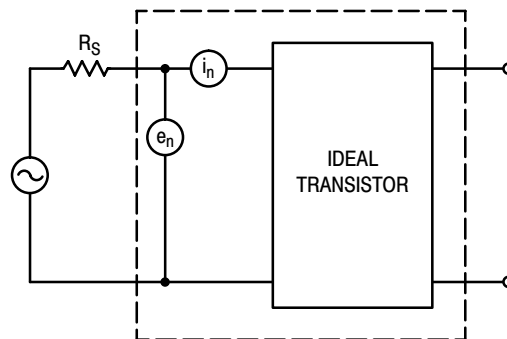


Figure 1. Transistor Noise Model

# BC549C, BC550C

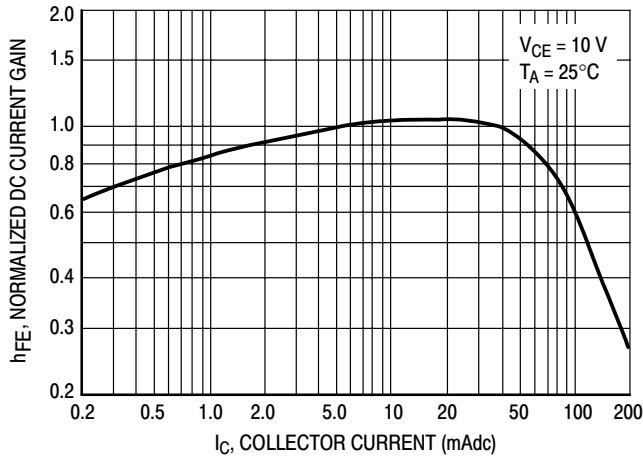


Figure 2. Normalized DC Current Gain

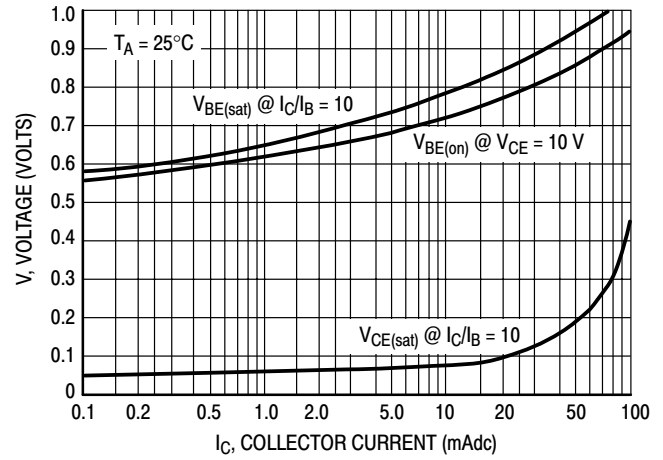


Figure 3. "Saturation" and "On" Voltages

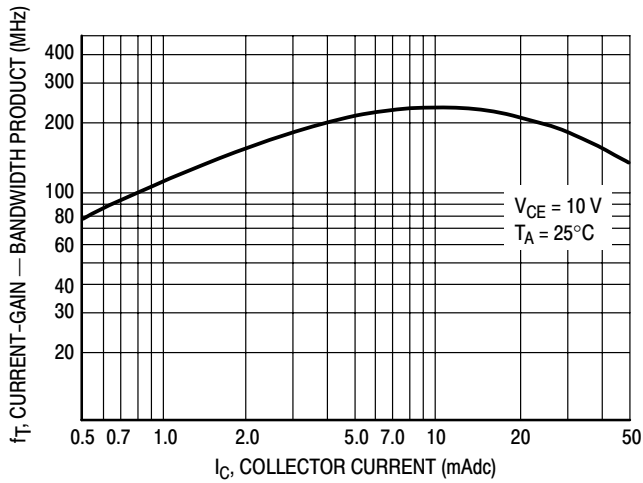


Figure 4. Current-Gain — Bandwidth Product

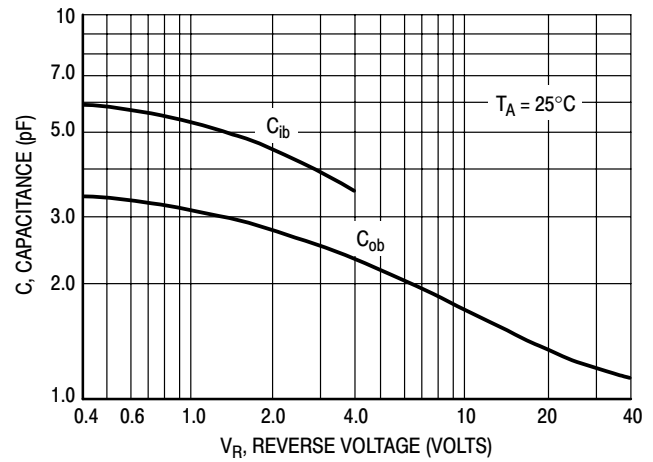


Figure 5. Capacitance

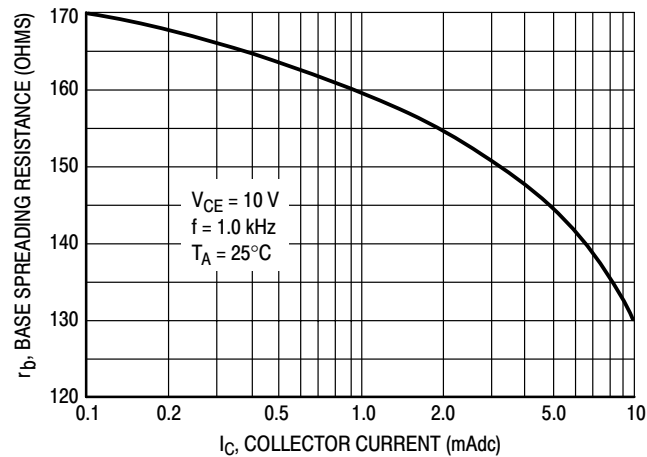


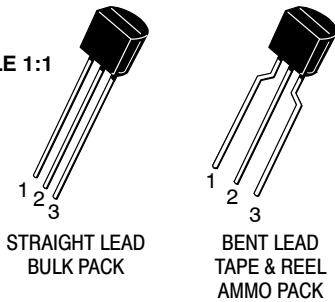
Figure 6. Base Spreading Resistance

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®

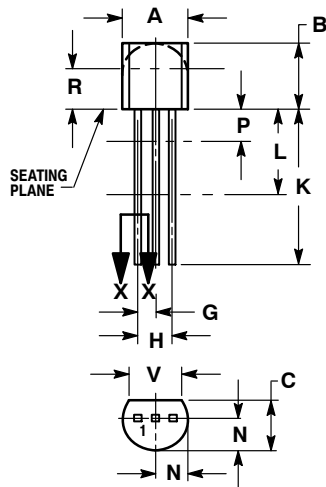
ON

SCALE 1:1

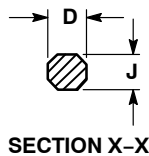


TO-92 (TO-226)  
CASE 29-11  
ISSUE AM

DATE 09 MAR 2007



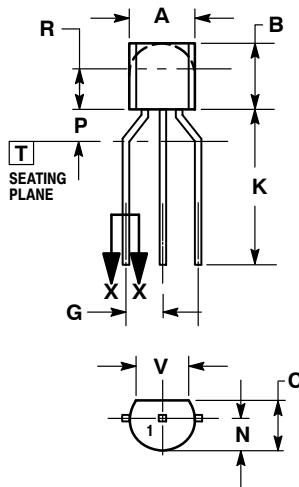
STRAIGHT LEAD  
BULK PACK



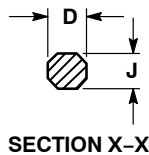
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD  
TAPE & REEL  
AMMO PACK



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42022B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
STATUS:	ON SEMICONDUCTOR STANDARD	
NEW STANDARD:		
DESCRIPTION:	TO-92 (TO-226)	
		PAGE 1 OF 3


**TO-92 (TO-226)**  
**CASE 29-11**  
**ISSUE AM**

DATE 09 MAR 2007

STYLE 1: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 2: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. DRAIN 2. SOURCE 3. GATE
STYLE 6: PIN 1. GATE 2. SOURCE & SUBSTRATE 3. DRAIN	STYLE 7: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 8: PIN 1. DRAIN 2. GATE 3. SOURCE & SUBSTRATE	STYLE 9: PIN 1. BASE 1 2. EMITTER 3. BASE 2	STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 11: PIN 1. ANODE 2. CATHODE & ANODE 3. CATHODE	STYLE 12: PIN 1. MAIN TERMINAL 1 2. GATE 3. MAIN TERMINAL 2	STYLE 13: PIN 1. ANODE 1 2. GATE 3. CATHODE 2	STYLE 14: PIN 1. EMITTER 2. COLLECTOR 3. BASE	STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2
STYLE 16: PIN 1. ANODE 2. GATE 3. CATHODE	STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER	STYLE 18: PIN 1. ANODE 2. CATHODE 3. NOT CONNECTED	STYLE 19: PIN 1. GATE 2. ANODE 3. CATHODE	STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE
STYLE 21: PIN 1. COLLECTOR 2. EMITTER 3. BASE	STYLE 22: PIN 1. SOURCE 2. GATE 3. DRAIN	STYLE 23: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 24: PIN 1. EMITTER 2. COLLECTOR/ANODE 3. CATHODE	STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2
STYLE 26: PIN 1. $V_{CC}$ 2. GROUND 2 3. OUTPUT	STYLE 27: PIN 1. MT 2. SUBSTRATE 3. MT	STYLE 28: PIN 1. CATHODE 2. ANODE 3. GATE	STYLE 29: PIN 1. NOT CONNECTED 2. ANODE 3. CATHODE	STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE
STYLE 31: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 32: PIN 1. BASE 2. COLLECTOR 3. EMITTER	STYLE 33: PIN 1. RETURN 2. INPUT 3. OUTPUT	STYLE 34: PIN 1. INPUT 2. GROUND 3. LOGIC	STYLE 35: PIN 1. GATE 2. COLLECTOR 3. EMITTER

<b>DOCUMENT NUMBER:</b>	<b>98ASB42022B</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>STATUS:</b>	<b>ON SEMICONDUCTOR STANDARD</b>	
<b>NEW STANDARD:</b>		
<b>DESCRIPTION:</b>	<b>TO-92 (TO-226)</b>	<b>PAGE 2 OF 3</b>

[illegible]

**ON Semiconductor** and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Email Requests to: [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

ON Semiconductor Website: [www.onsemi.com](http://www.onsemi.com)

### TECHNICAL SUPPORT

#### North American Technical Support:

Voice Mail: 1 800-282-9855 Toll Free USA/Canada

Phone: 011 421 33 790 2910

#### Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative